

ABSTRACT OF THE DISCLOSURE (FIG. 10)

"DEVELOPING METHOD"

A developing method comprising the steps of (a) keeping a wafer substantially horizontally such that a resist-coated surface is placed at a top portion,
5 (b) starting a rotation of the wafer at a first speed N1, starting discharging developer from a nozzle at a position where the wafer is prevented from being applied thereon during the rotation of the wafer, and
10 starting scan-moving the nozzle along the wafer as discharging developer, (c) starting a first deceleration for decelerating the rotation of the wafer while the nozzle is scan-moving, (d) stopping the scan-movement of the nozzle above a central area of the
15 wafer when the rotation of the wafer reaches a second speed N2, (e) ending the first deceleration when the rotation of the wafer reaches a third speed N3, and (f) starting a second deceleration for decelerating the rotation of the wafer from the third speed N3 to a
20 fourth speed N4 after rotating the wafer at the third speed N3, ending the second deceleration when the rotation of the wafer reaches at the fourth speed N4, and supplying developer onto the wafer while the wafer is being rotated at the fourth speed N4 such that a
25 liquid film of developer having a uniform thickness is formed on the wafer to develop the resist coated on the wafer.